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Team Nexperia

## PEMH10; PUMH10

# NPN/NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47k $\Omega$

Rev. 3 — 20 December 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number			NPN/PNP	PNP/PNP	Package	
	NXP	JEITA	complement	complement	configuration	
PEMH10	SOT666	-	PEMD10	PEMB10	ultra small and flat lead	
PUMH10	SOT363	SC-88	PUMD10	PUMB10	very small	

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



### 2. Pinning information

Table 3. Pinning

Table 3.	rinning			
Pin	Description	Simplified outline	Graphic symbol	
1	GND (emitter) TR1			
2	input (base) TR1	6   5   4	6 5 4	
3	output (collector) TR2			
4	GND (emitter) TR2		R1 R2	
5	input (base) TR2		TR1	
6	output (collector) TR1	001aab555	R2 R1 R1 1 2 3	
			sym063	

### 3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMH10	-	plastic surface-mounted package; 6 leads	SOT666	
PUMH10	SC-88	plastic surface-mounted package; 6 leads	SOT363	

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMH10	10
PUMH10	H*0

<sup>[1] \* =</sup> placeholder for manufacturing site code.

### 5. Limiting values

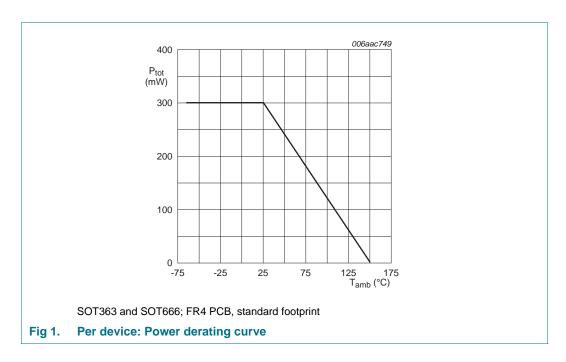
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	5	V
VI	input voltage				
	positive		-	+12	V
	negative		-	<b>-</b> 5	V
Io	output current		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mΑ
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u>		
	PEMH10 (SOT666)		[2] _	200	mW
	PUMH10 (SOT363)		-	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25~^{\circ}C$	<u>[1]</u>		
	PEMH10 (SOT666)		[2] _	300	mW
	PUMH10 (SOT363)		-	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



#### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMH10 (SOT666)		[2] _	-	625	K/W
	PUMH10 (SOT363)		-	-	625	K/W
Per device	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMH10 (SOT666)		[2] _	-	417	K/W
	PUMH10 (SOT363)		-	-	417	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

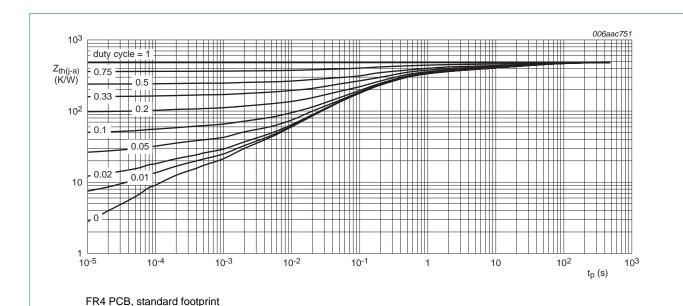


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH10 (SOT666); typical values

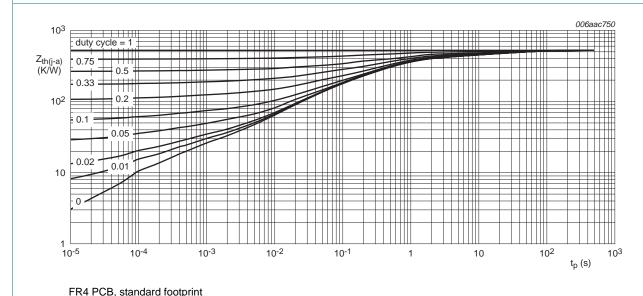


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH10 (SOT363); typical values

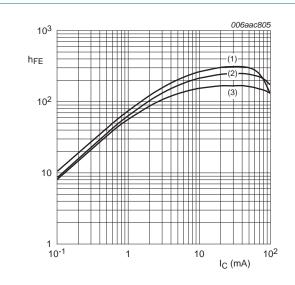
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
Per trans	istor						
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-		-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-		-	100	nA
cut-off	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-		-	5	μА
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-		-	180	μА
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	1	00	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	-		-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-		0.6	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	1	.1	0.75	-	V
R1	bias resistor 1 (input)		1	.54	2.20	2.86	$k\Omega$
R2/R1	bias resistor ratio		1	7	21	26	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-		-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CB} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	[1] -		230	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor.



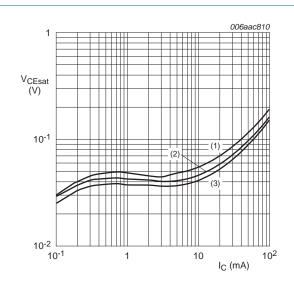
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



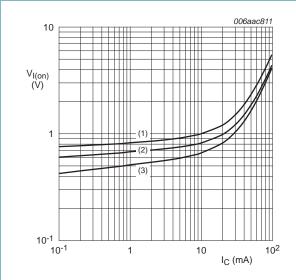
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



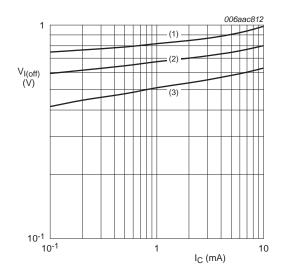
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

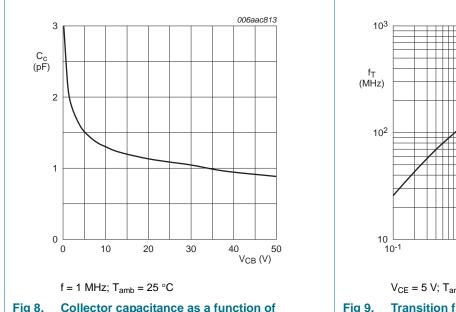


Fig 8. Collector capacitance as a function of collector-base voltage; typical values

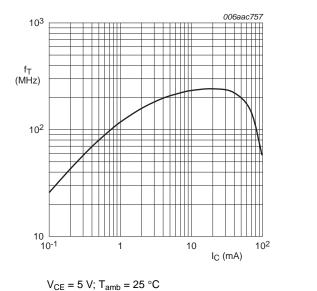


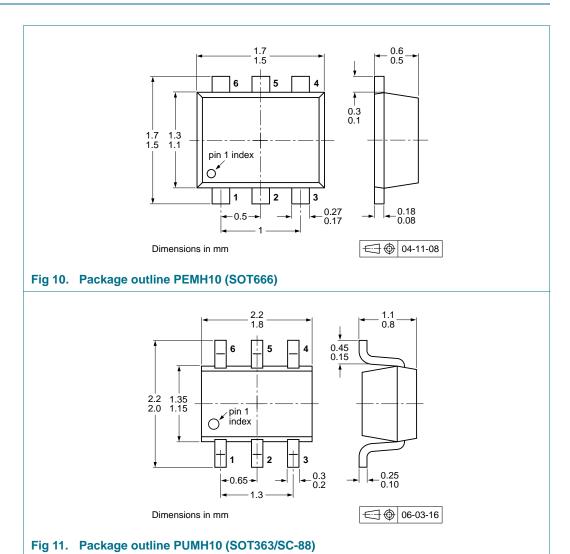
Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

#### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



### 10. Packing information

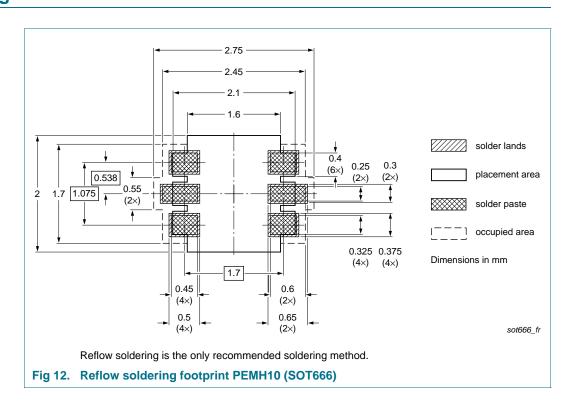
Table 9. Packing methods

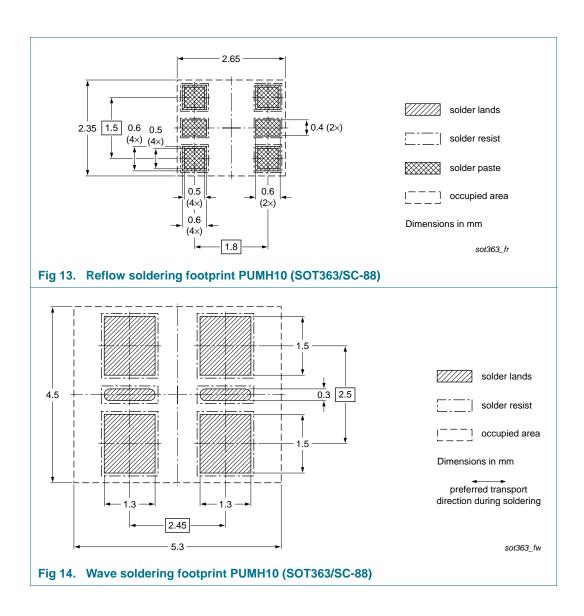
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packi	ng quai	ntity	
				3000	4000	8000	10000
PEMH10	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH10	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

### 11. Soldering





### 12. Revision history

#### Table 10. Revision history

Danis and ID	Deleges dete	Data about status	01	0			
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PEMH10_ PUMH10 v.3	20111220	Product data sheet	-	PEMH10_ PUMH10 v.2			
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section 1 "Product profile": updated</li> <li>Section 4 "Marking": updated</li> <li>Table 7 "Thermal characteristics": updated according to the latest measurements</li> <li>Table 8 "Characteristics": I<sub>CEO</sub> updated according to the latest measurements, f<sub>T</sub> added, V<sub>i(off)</sub> redefined to V<sub>I(off)</sub> off-state input voltage, V<sub>i(on)</sub> redefined to V<sub>I(on)</sub> on-state input voltage.</li> </ul>						
	<ul> <li><u>Figure 1</u> to <u>9</u>: added</li> <li><u>Section 8 "Test information"</u>: added</li> </ul>						
		• Figure 10 and 11: replaced by minimized package outline drawings					
		acking information": adde	d				
	<ul> <li>Section 11 "So</li> </ul>	oldering": added					
	<ul> <li>Section 13 "Le</li> </ul>	egal information": updated					
PEMH10_ PUMH10 v.2	20031020	Product data sheet	-	PEMH10 v.1			
				PUMH10 v.1			
PEMH10 v.1	20011022	Preliminary specification	on -	-			
PUMH10 v.1	20000801	Product specification		-			

#### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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PEMH10\_PUMH10

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PEMH10; PUMH10

NPN/NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47k $\Omega$ 

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